

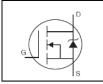
AUTOMOTIVE GRADE

AUIRFR4292 AUIRFU4292

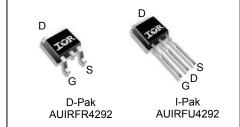
Features

- Advanced Process Technology
- Low On-Resistance
- 175°C Operating Temperature
- Fast Switching
- Repetitive Avalanche Allowed up to Tjmax

- Lead-Free, RoHS Compliant
- Automotive Qualified *



V _{DSS}		250V
R _{DS(on)}	typ.	275mΩ
	max.	345mΩ
I _D		9.3A



realures of this design are a 175 C junction operating temperature,			
fast switching speed and improved repetitive avalanche rating.	G	D	S
These features combine to make this design an extremely efficient		Drain	Source
and reliable device for use in Automotive applications and a wide ¹			

Description Specifically designed for Automotive applications, this HEXFET® Power MOSFET utilizes the latest processing techniques to achieve extremely low on-resistance per silicon area. Additional	D S G D-Pak AUIRFR4292	S G ^D I-Pak AUIRFU4292	
features of this design are a 175°C junction operating temperature,	1		_

Book most musebox	Dookses Tyme	Standard Pack		Oudenshie Deut Neumhen	Note	
Base part number	Package Type	Form	Quantity	Orderable Part Number	Note	
AUIRFU4292	I-Pak	Tube	75	AUIRFU4292		
		Tube	75	AUIRFR4292		
AUIRFR4292	D-Pak	Tape and Reel Left	3000	AUIRFR4292TRL		
		Tape and Reel Right	3000	AUIRFR4292TRR	EOL notice #530	

Absolute Maximum Ratings

variety of other applications.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only; and functional operation of the device at these or any other condition beyond those indicated in the specifications is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions. Ambient temperature (TA) is 25°C, unless otherwise specified.

Symbol	Parameter	Max.	Units
I _D @ T _C = 25°C	Continuous Drain Current, V _{GS} @ 10V	9.3	
I _D @ T _C = 100°C	Continuous Drain Current, V _{GS} @ 10V	6.6	Α
I _{DM}	Pulsed Drain Current ①	40	
$P_D @ T_C = 25^{\circ}C$	Maximum Power Dissipation	100	W
	Linear Derating Factor	0.67	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
E _{AS}	Single Pulse Avalanche Energy (Thermally Limited) ②	130	
E _{AS} (Tested)	Single Pulse Avalanche Energy Tested Value ®	97	mJ
I _{AR}	Avalanche Current ①	See Fig.15,16, 12a, 12b	Α
E _{AR}	Repetitive Avalanche Energy S		mJ
T _J	Operating Junction and	-55 to + 175	
T _{STG}	Storage Temperature Range		°C
	Soldering Temperature, for 10 seconds (1.6mm from case)	300	

Thermal Resistance

Symbol	Parameter	Тур.	Max.	Units
$R_{\theta JC}$	Junction-to-Case		1.5	
$R_{\theta JA}$	Junction-to-Ambient (PCB Mount) ∅		50	°C/W
$R_{\theta JA}$	Junction-to-Ambient		110	

HEXFET® is a registered trademark of Infineon.

2015-10-12

^{*}Qualification standards can be found at www.infineon.com



Static @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Тур.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	250			V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient		0.31		V/°C	Reference to 25°C, I _D = 1mA
R _{DS(on)}	Static Drain-to-Source On-Resistance		275	345	mΩ	V _{GS} = 10V, I _D = 5.6A ③
$V_{GS(th)}$	Gate Threshold Voltage	3.0		5.0	V	$V_{DS} = V_{GS}$, $I_D = 50\mu A$
gfs	Forward Trans conductance	6.2			S	$V_{DS} = 50V, I_{D} = 5.6A$
	Drain-to-Source Leakage Current			20	μA	$V_{DS} = 250 \text{ V}, V_{GS} = 0 \text{V}$
IDSS	Drain-to-Source Leakage Current			250	μΑ	$V_{DS} = 250V, V_{GS} = 0V, T_{J} = 125^{\circ}C$
	Gate-to-Source Forward Leakage			200	- Δ	V _{GS} = 20V
I _{GSS}	Gate-to-Source Reverse Leakage			-200	nA	$V_{GS} = -20V$

Dynamic Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

Q_g	Total Gate Charge	 13	20		$I_{D} = 5.6A$
Q_{gs}	Gate-to-Source Charge	 4.7		nC	V _{DS} = 125V
$\overline{Q_{gd}}$	Gate-to-Drain Charge	 4.8			V _{GS} = 10V3
$t_{d(on)}$	Turn-On Delay Time	 11			V _{DD} = 250V
t _r	Rise Time	 15		no	$I_D = 5.6A$
$t_{d(off)}$	Turn-Off Delay Time	 16		ns	$R_G = 15\Omega$
t _f	Fall Time	 8.4			V _{GS} = 10V3
L _D	Internal Drain Inductance	 4.5			Between lead, 6mm (0.25in.)
L _S	Internal Source Inductance	 7.5			from package and center of die contact
C _{iss}	Input Capacitance	 705			$V_{GS} = 0V$
Coss	Output Capacitance	 71			$V_{DS} = 25V$
C_{rss}	Reverse Transfer Capacitance	 20		рF	f = 1.0 MHz
C _{oss}	Output Capacitance	 600		PΓ	$V_{GS} = 0V, V_{DS} = 1.0V f = 1.0MHz$
C _{oss}	Output Capacitance	 26			$V_{GS} = 0V, V_{DS} = 200V f = 1.0MHz$
Coss eff.	Effective Output Capacitance	 65			$V_{GS} = 0V, V_{DS} = 0V \text{ to } 200V $
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Diode Characteristics

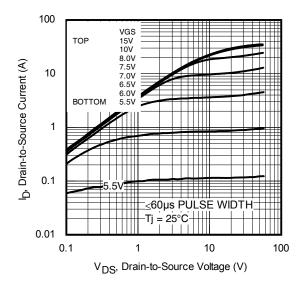
	Parameter	Min.	Тур.	Max.	Units	Conditions
I _S	Continuous Source Current (Body Diode)			9.3	_	MOSFET symbol showing the
I _{SM}	Pulsed Source Current (Body Diode) ①			40		integral reverse p-n junction diode.
V_{SD}	Diode Forward Voltage			1.3	V	$T_J = 25^{\circ}C, I_S = 5.6A, V_{GS} = 0V$ 3
t _{rr}	Reverse Recovery Time		110	165	ns	$T_J = 25^{\circ}C$, $I_F = 5.6A$, $V_{DD} = 125V$
Q_{rr}	Reverse Recovery Charge		390	585	nC	di/dt = 100A/µs③
t _{on}	Forward Turn-On Time	Intrinsio	turn-or	time is	negligil	ole (turn-on is dominated by L _S +L _D)

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)
- ② Limited by T_{Jmax} , starting $T_J = 25$ °C, L = 8.1mH, $R_G = 50\Omega$, $I_{AS} = 5.6$ A, $V_{GS} = 10$ V. Part not recommended for use above this value.
- \oplus C_{oss} eff. is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS}
- © Limited by T_{Jmax}, see Fig.12a, 12b, 15, 16 for typical repetitive avalanche performance.
- When mounted on 1" square PCB (FR-4 or G-10 Material). For recommended footprint and soldering techniques refer to application note #AN-994

R_θ is measured at T_J approximately 90°C





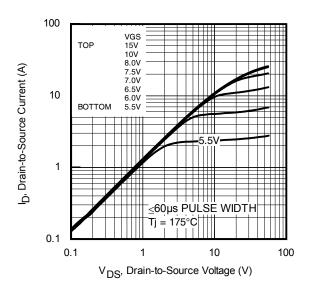
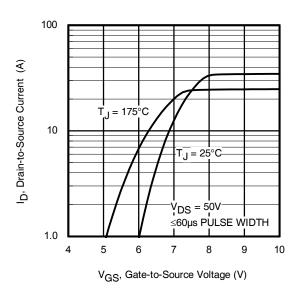


Fig. 1 Typical Output Characteristics

Fig. 2 Typical Output Characteristics





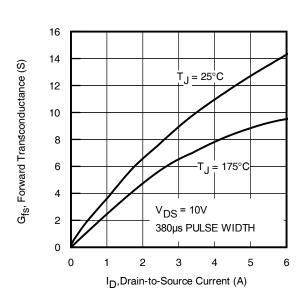


Fig. 4 Typical Forward Transconductance Vs. Drain Current



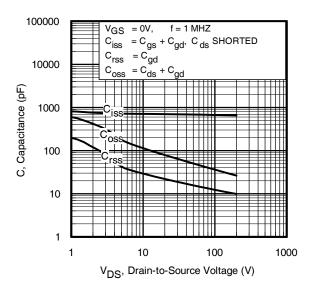


Fig 5. Typical Capacitance vs. Drain-to-Source Voltage

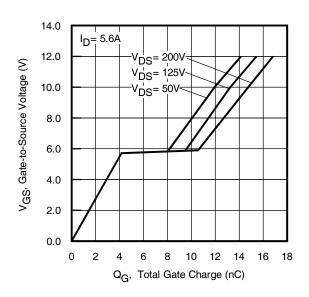


Fig 6. Typical Gate Charge vs. Gate-to-Source Voltage

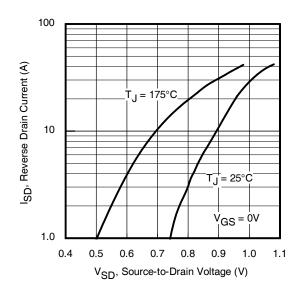


Fig. 7 Typical Source-to-Drain Diode Forward Voltage

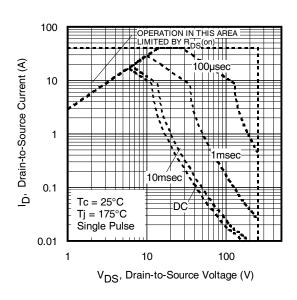
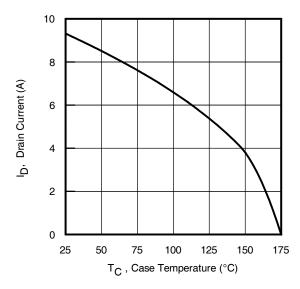


Fig 8. Maximum Safe Operating Area

4





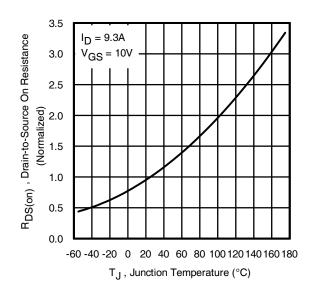


Fig 9. Maximum Drain Current Vs. Case Temperature

Fig 10. Normalized On-Resistance Vs. Temperature

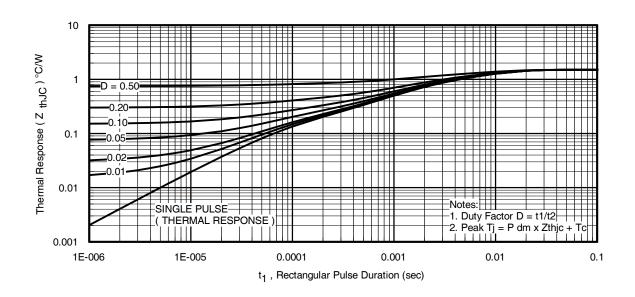


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case



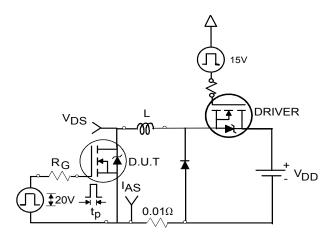


Fig 12a. Unclamped Inductive Test Circuit

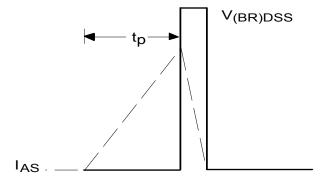


Fig 12b. Unclamped Inductive Waveforms

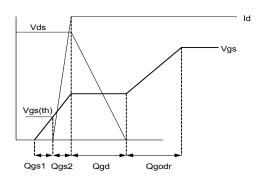


Fig 13a. Gate Charge Waveform

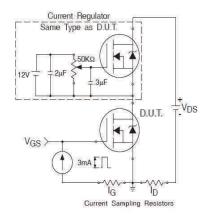


Fig 13b. Gate Charge Test Circuit

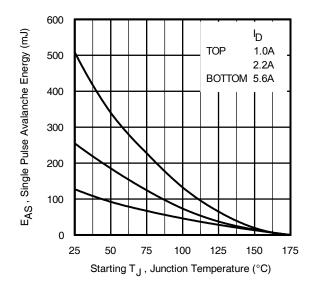


Fig 12c. Maximum Avalanche Energy vs. Drain Current

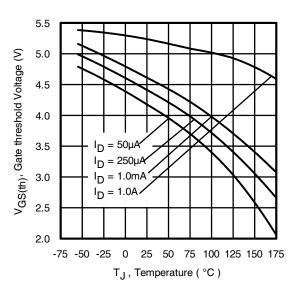


Fig 14. Threshold Voltage Vs. Temperature

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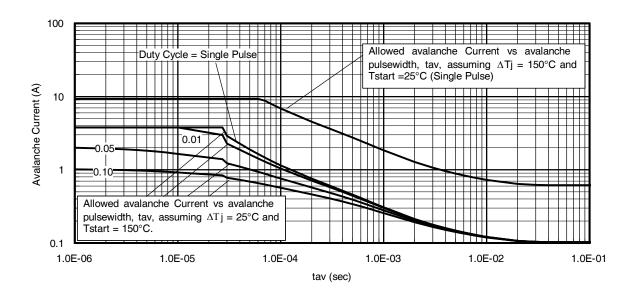


Fig 15. Typical Avalanche Current Vs. Pulse width

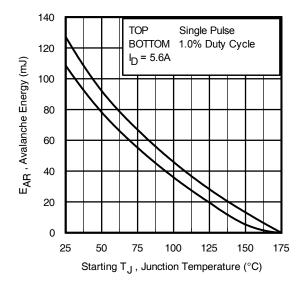


Fig 16. Maximum Avalanche Energy Vs. Temperature

Notes on Repetitive Avalanche Curves , Figures 15, 16:

(For further info, see AN-1005 at www.infineon.com)

- Avalanche failures assumption:
 Purely a thermal phenomenon and failure occurs at a temperature far in excess of T_{imax}. This is validated for every part type.
- 2. Safe operation in Avalanche is allowed as long as T_{jmax} is not exceeded.
- 3. Equation below based on circuit and waveforms shown in Figures 12a, 12b.
- 4. PD (ave) = Average power dissipation per single avalanche pulse.
- 5. BV = Rated breakdown voltage (1.3 factor accounts for voltage increase during avalanche).
- 6. lav = Allowable avalanche current.
- 7. ΔT = Allowable rise in junction temperature, not to exceed T_{jmax} (assumed as 25°C in Figure 15, 16).

tav = Average time in avalanche.

D = Duty cycle in avalanche = tav ·f

ZthJC(D, tav) = Transient thermal resistance, see Figures 13)

$$\begin{split} P_{D \; (ave)} &= 1/2 \; (\; 1.3 \cdot BV \cdot I_{av}) = \Delta T / \; Z_{thJC} \\ I_{av} &= 2\Delta T / \; [1.3 \cdot BV \cdot Z_{th}] \\ E_{AS \; (AR)} &= P_{D \; (ave)} \cdot t_{av} \end{split}$$

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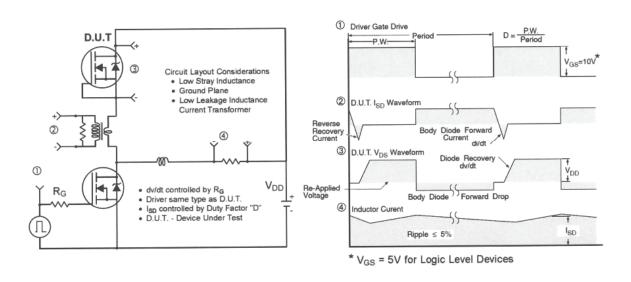


Fig 17. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs

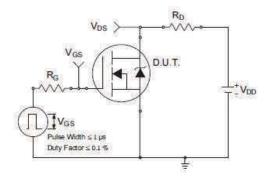


Fig 18a. Switching Time Test Circuit

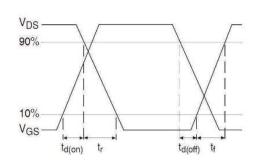
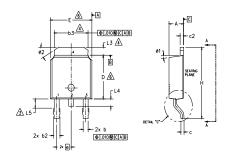


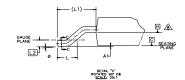
Fig 18b. Switching Time Waveforms

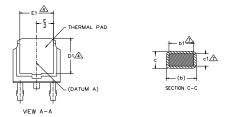


D-Pak (TO-252AA) Package Outline (Dimensions are shown in millimeters (inches))









NOTES:

- 1.- DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
- 2.- DIMENSION ARE SHOWN IN INCHES [MILLIMETERS].
- LEAD DIMENSION UNCONTROLLED IN L5.
- A- DIMENSION D1, E1, L3 & b3 ESTABLISH A MINIMUM MOUNTING SURFACE FOR THERMAL PAD.
- 5.— SECTION C-C DIMENSIONS APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN .005 AND 0.10 [0.13 AND 0.25] FROM THE LEAD TIP.
- Limited Dimension D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005 [0.13] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
- A- DIMENSION b1 & c1 APPLIED TO BASE METAL ONLY.
- ♠ DATUM A & B TO BE DETERMINED AT DATUM PLANE H.
- 9.- OUTLINE CONFORMS TO JEDEC OUTLINE TO-252AA.

S Y M B DIMENSIONS N O T E M B B B B B B B B B B B B B B B B B B B							
B O L MINLIMETERS INCHES T E S E S E S E S E S E S E S E S E S E			DIMENSIONS				
A 2.18 2.39 .086 .094 A1 - 0.13005 b 0.64 0.89 .025 .035 b1 0.65 0.79 .025 .031 7 b2 0.76 1.14 .030 .045 b3 4.95 5.46 .195 .215 4 c 0.46 0.61 .018 .022 7 c2 0.46 0.89 .018 .035 D 5.97 6.22 .235 .245 6 D1 5.21205 - 4 E 6.35 6.73 .250 .265 6 E1 4.32170 - 4 E 6.35 6.73 .250 .265 6 E1 4.32170 - 4 E 2.29 BSC .090 BSC H 9.40 10.41 .370 .410 L 1.40 1.78 .055 .070 L1 2.74 BSC .108 REF. L2 0.51 BSC .020 BSC L3 0.89 1.27 .035 .050 4 L4102040 L5 1.14 1.52 .045 .060 3 Ø 0° 10° 0° 10° Ø1 0° 15° 0° 15°	В	MILLIM	ETERS	INC	HES	Ť	
A1 - 0.13 - .005 b 0.64 0.89 .025 .035 b1 0.65 0.79 .025 .031 7 b2 0.76 1.14 .030 .045 b3 4.95 5.46 .195 .215 4 c 0.46 0.61 .018 .024 7 c2 0.46 0.89 .018 .035 6 D 5.97 6.22 .235 .245 6 D1 5.21 - .205 - 4 E 6.35 6.73 .250 .265 6 E1 4.32 - .170 - 4 e 2.29 BSC .090 BSC H 9.40 10.41 .370 .410 L 1.40 1.78 .055 .070 L1 2.74 BSC .108 REF.		MIN.	MAX.	MIN.	MAX.	E S	
b 0.64 0.89 .025 .035 b1 0.65 0.79 .025 .031 7 b2 0.76 1.14 .030 .045 b3 4.95 5.46 .195 .215 4 c 0.46 0.61 .018 .024 7 c1 0.41 0.56 .016 .022 7 c2 0.46 0.89 .018 .035 D 5.97 6.22 .235 .245 6 D1 5.21 - .205 - 4 E 6.35 6.73 .250 .265 6 E1 4.32 - .170 - 4 e 2.29 BSC .090 BSC H 9.40 10.41 .370 .410 L 1.140 1.78 .055 .070 L1 2.74 BSC .108 REF. <tr< td=""><td>Α</td><td>2.18</td><td>2.39</td><td>.086</td><td>.094</td><td></td></tr<>	Α	2.18	2.39	.086	.094		
b1 0.65 0.79 .025 .031 7 b2 0.76 1.14 .030 .045 b3 4.95 5.46 .195 .215 4 c 0.46 0.61 .018 .024 7 c2 0.46 0.89 .018 .035 6 D 5.97 6.22 .235 .245 6 D1 5.21 — .205 — 4 E 6.35 6.73 .250 .265 6 E1 4.32 — .170 — 4 e 2.29 BSC .090 BSC H 9.40 10.41 .370 .410 L 1.40 1.78 .055 .070 L1 2.74 BSC .108 REF. L2 0.51 BSC .020 BSC L3 0.89 1.27 .035 .050 4	A1	_	0.13	-	.005		
b2 0.76 1.14 0.30 0.045 b3 4.95 5.46 .195 .215 4 c 0.46 0.61 .018 .024 7 c1 0.41 0.56 .016 .022 7 c2 0.46 0.89 .018 .035 D 5.97 6.22 .235 .245 6 D1 5.21 - .205 - 4 E 6.35 6.73 .250 .265 6 E1 4.32 - .170 - 4 e 2.29 BSC .090 BSC H 9.40 10.41 .370 .410 L 1.40 1.78 .055 .070 L1 2.74 BSC .108 REF. L2 0.51 BSC .020 BSC L3 0.89 1.27 .035 .050 4	b	0.64	0.89	.025	.035		
b3	ь1	0.65	0.79	.025	.031	7	
c 0.46 0.61 .018 .024 c1 0.41 0.56 .016 .022 7 c2 0.46 0.89 .018 .035 6 D 5.97 6.22 .235 .245 6 D1 5.21 - .205 - 4 E 6.35 6.73 .250 .265 6 E1 4.32 - .170 - 4 e 2.29 BSC .090 BSC H 9.40 10.41 .370 .410 L 1.40 1.78 .055 .070 L1 2.74 BSC .108 REF. L2 0.51 BSC .020 BSC L3 0.89 1.27 .035 .050 4 L4 - 1.02 - .040 L5 1.14 1.52 .045 .060 3	b2	0.76	1.14	.030	.045		
c1 0.41 0.56 .016 .022 7 c2 0.46 0.89 .018 .035 6 D 5.97 6.22 .235 .245 6 D1 5.21 - .205 - 4 E 6.35 .250 .265 6 E1 4.32 - .170 - 4 e 2.29 BSC .090 BSC H 9.40 10.41 .370 .410 L 1.40 1.78 .055 .070 L1 2.74 BSC .108 REF. L2 0.51 BSC .020 BSC L3 0.89 1.27 .035 .050 4 L4 - 1.02 - .040 L5 1.14 1.52 .045 .060 3 Ø 0° 10° 0° 10° 10° Ø	b3	4.95	5.46	.195	.215	4	
c2 0.46 0.89 .018 .035 D 5.97 6.22 .235 .245 6 D1 5.21 - .205 - 4 E 6.35 6.73 .250 .265 6 E1 4.32 - .170 - 4 e 2.29 BSC .090 BSC H 9.40 10.41 .370 .410 L 1.40 1.78 .055 .070 L1 2.74 BSC .108 REF. L2 0.51 BSC .020 BSC L3 0.89 1.27 .035 .050 4 L4 - 1.02 - .040 L5 1.14 1.52 .045 .060 3 Ø 0° 10° 0° 10° Ø 0° 10° 0° 15°	С	0.46	0.61	.018	.024		
D 5.97 6.22 .235 .245 6	c1	0.41	0.56	.016	.022	7	
D1	c2	0.46	0.89	.018	.035		
E 6.35 6.73 .250 .265 6 E1 4.32170 - 4 e 2.29 BSC .090 BSC H 9.40 10.41 .370 .410 L 1.40 1.78 .055 .070 L1 2.74 BSC .108 REF. L2 0.51 BSC .020 BSC L3 0.89 1.27 .035 .050 4 L4 - 1.02040 L5 1.14 1.52 .045 .060 3 Ø 0' 10' 0' 10' Ø1 0' 15' 0' 15'	D	5.97	6.22	.235	.245	6	
E1 4.32 - .170 - 4 e 2.29 BSC .090 BSC H 9.40 10.41 .370 .410 L 1.40 1.78 .055 .070 L1 2.74 BSC .108 REF. L2 0.51 BSC .020 BSC L3 0.89 1.27 .035 .050 4 L4 - 1.02 - .040 L5 1.14 1.52 .045 .060 3 Ø 0° 10° 0° 10° Ø1 0° 15° 0° 15°	D1	5.21	-	.205	-	4	
e 2.29 BSC .090 BSC H 9.40 10.41 .370 .410 L 1.40 1.78 .055 .070 L1 2.74 BSC .108 REF. L2 0.51 BSC .020 BSC L3 0.89 1.27 .035 .050 4 L4 - 1.02 - .040 L5 1.14 1.52 .045 .060 3 Ø 0° 10° 0° 10° 0° 15° Ø1 0° 15° 0° 15° 0° 15°	Ε	6.35	6.73	.250	.265	6	
H 9.40 10.41 .370 .410	E1	4.32	-	.170	-	4	
L 1.40 1.78 .055 .070 L1 2.74 BSC .108 REF. L2 0.51 BSC .020 BSC L3 0.89 1.27 .035 .050 4 L4 - 1.02040 L5 1.14 1.52 .045 .060 3 Ø 0° 10° 0° 10° 0° 10° Ø1 0° 15° 0° 15°	е	2.29	BSC	.090	BSC		
L1	Н	9.40	10.41	.370	.410		
L2 0.51 BSC .020 BSC L3 0.89 1.27 .035 .050 4 L4 - 1.02 - .040 .045 .060 3 Ø 0° 10° 0° 10° 9 15° 15° 15°	L	1.40	1.78	.055	.070		
L3 0.89 1.27 .035 .050 4 L4 - 1.02040 L5 1.14 1.52 .045 .060 3 Ø 0° 10° 0° 10° Ø1 0° 15° 0° 15°	L1	2.74	BSC	.108	REF.		
L4 - 1.02 - .040 L5 1.14 1.52 .045 .060 3 Ø 0° 10° 0° 10° Ø1 0° 15° 0° 15°	L2	0.51	BSC	.020	BSC		
L5 1.14 1.52 .045 .060 3 ø 0° 10° 0° 10° ø1 0° 15° 0° 15°	L3	0.89	1.27	.035	.050	4	
ø 0° 10° 0° 10° ø 0° 15° 0° 15°	L4	-	1.02	-	.040		
ø1 0° 15° 0° 15°	L5	1.14	1.52	.045	.060	3	
	ø	0.	10°	0,	10°		
ø2 25° 35° 25° 35°	ø1	0,	15*	0,	15*		
	ø2	25*	35°	25*	35*		

LEAD ASSIGNMENTS

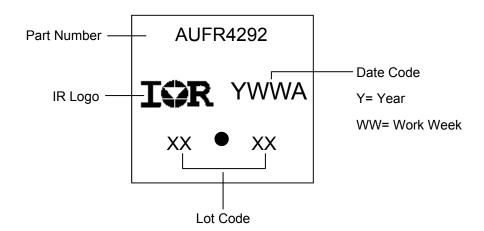
HEXFET

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

IGBT & CoPAK

- 1.- GATE
- 2.- COLLECTOR
- 3.- EMITTER
- 4. COLLECTOR

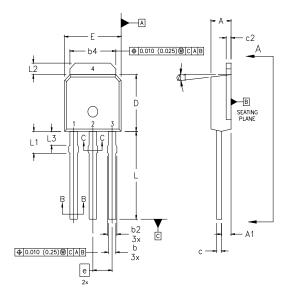
D-Pak (TO-252AA) Part Marking Information

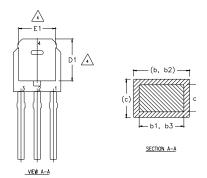


Note: For the most current drawing please refer to IR website at http://www.irf.com/package/



I-Pak (TO-251AA) Package Outline (Dimensions are shown in millimeters (inches)





NOTES:

SYMBOL

A1

b

ь1

b2

b4

c1 c2

D

D1

E1

e L

L1

L2

L3

- 1 DIMENSIONING AND TOLERANCING PER ASME Y14.5 M- 1994.
- 2 DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
- 3 DIMENSION D & E DO NOT INCLUDE MOLD FLASH, MOLD FLASH SHALL NOT EXCEED 0.005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
- 4 THERMAL PAD CONTOUR OPTION WITHIN DIMENSION 64, L2, E1 & D1.

INCHES

.094

0.045

0.035

0.031

0.045

0.041

0.215

0.024

0.022

0.035

0.245

0.265

0.380

0.090

0.050

0.060

15*

0.086

0.035

0.025

0.025

0.030

0.030

0.195

0.018

0.016

0.018

0.235

0.205

0.250

0.170

0.350

0.075

0.035

0.045

0.090 BSC

NOTES

LEAD DIMENSION UNCONTROLLED IN L3.

2.39

1.14

0.89

0.79

1.14

1.04

5.46

0.61

0.56

0.86

6.22

6.73

9.60

2.29

1.27

1.52

6 DIMENSION 61, 63 APPLY TO BASE METAL ONLY.
7 OUTLINE CONFORMS TO JEDEC OUTLINE TO-251AA.

DIMENSIONS

8 CONTROLLING DIMENSION : INCHES.

MILLIMETERS

MIN.

2.18

0.89

0.64

0.64

0.76

0.76

5.00

0.46

0.41

.046

5.97

5.21

6.35

4.32

8.89

1,91

0.89

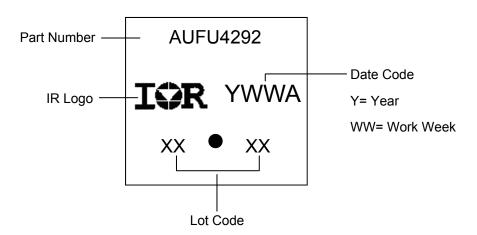
1.14

LEAD ASSIGNMENTS

<u>HEXFET</u>

- 1.- GATE 2.- DRAIN
- 3.- SOURCE 4.- DRAIN

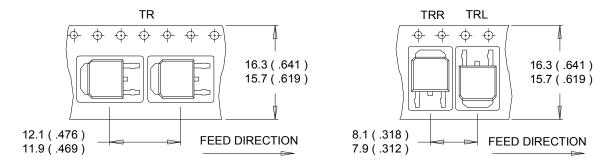
I-Pak (TO-251AA) Part Marking Information



Note: For the most current drawing please refer to IR website at http://www.irf.com/package/

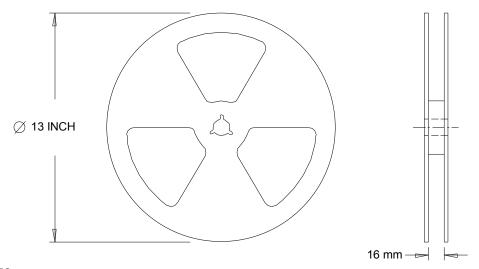


D-Pak (TO-252AA) Tape & Reel Information (Dimensions are shown in millimeters (inches))



NOTES:

- 1. CONTROLLING DIMENSION: MILLIMETER.
- 2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
- 3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



NOTES:

1. OUTLINE CONFORMS TO EIA-481.

Note: For the most current drawing please refer to IR website at http://www.irf.com/package/



Qualification Information

		Automotive (per AEC-Q101)				
		Comments: This part number(s) passed Automotive qualification. Infineon's Industrial and Consumer qualification level is granted by extension of the higher Automotive level.				
		D-Pak	MSL1			
Woisture	Moisture Sensitivity Level		IVISL I			
	Machine Model	Class M1B (+/- 100V) [†]				
	Machine Model	AEC-Q101-002				
ECD	Lluman Dady Madal	Class H1A (+/- 500V) [†]				
E2D	ESD Human Body Model		AEC-Q101-001			
	Channed Davisa Madal	Class C5 (+/- 2000V) [†]				
Charged Device Model		AEC-Q101-005				
RoHS Compliant		Yes				

† Highest passing voltage.

Revision History

Date	Comments					
	Updated datasheet with IR corporate tempalte.					
• Updated SOA curve Fig 8 from "50V" V _{DS} to "250V" on page 4.						
9/2/2014	Updated Package outline on page 9 & 10					
	Updated ordering information to reflect the End-Of-life (EOL) of the option (EOL notice #530)					
10/12/2015	Updated datasheet with corporate template					
10/12/2013	Corrected ordering table on page 1.					

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